

isc Silicon NPN Power Transistor

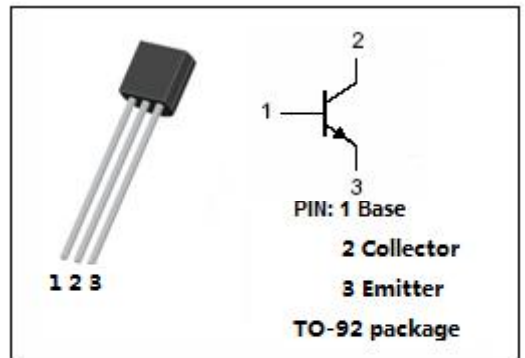
2SC2705

DESCRIPTION

- Collector-Emitter sustaining Voltage : $V_{CEO}=150V(\text{Min})$
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

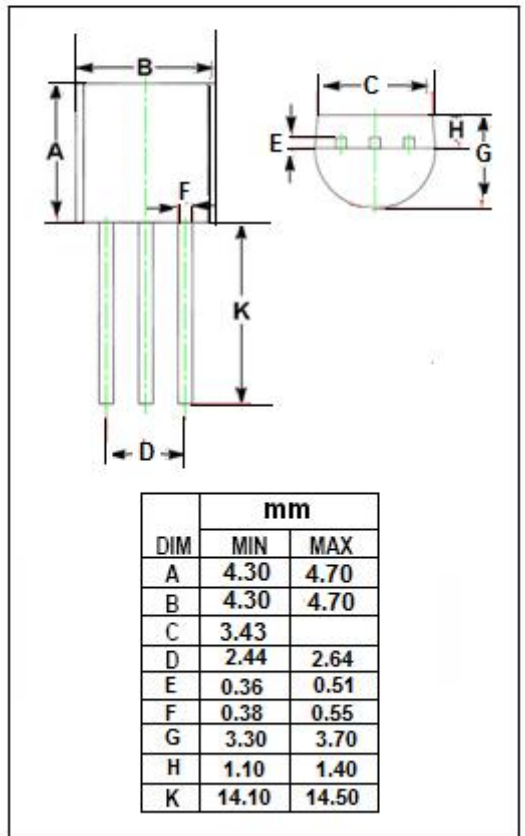
APPLICATIONS

- Audio Frequency Amplifier Applications



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	50	mA
I_B	Base Current- Continuous	5	mA
P_C	Total Power Dissipation @ $T_C=25^{\circ}C$	800	mW
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(BR)}	Collector-Emitter Breakdown Voltage	I _c =30mA ; I _B = 0	150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _c = 10mA; I _B = 1mA			1.0	V
V _{BE(sat)}	Base-Emitter Voltage	I _c = 10mA; V _{CE} =5V			0.8	V
I _{CEO}	Collector Cutoff Current	V _{CE} = 150V ; I _E = 0			0.1	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} =5V; I _C = 0			0.1	μA
h _{FE}	DC Current Gain	I _c =10mA ; V _{CE} =5V	80		240	